1.

Record Nr.	UNISALENTO991002616149707536
Autore	Ferlino, Lucia
Titolo	Didattica e disabilità : quale software? / Lucia Ferlino, Michela Ott, Guglielmo Trentin
Pubbl/distr/stampa	Milano : F. Angeli, 1993
Descrizione fisica	367 p ; 22cm
Collana	Didattica : temi e problemi
Altri autori (Persone)	Ott, Michelaauthor Trentin, Guglielmoauthor
Soggetti	Handicap e Scuola Informatica - Applicazioni alla didattica Informatica scolastica
Lingua di pubblicazione	Italiano
Formato	Materiale a stampa
Livello bibliografico	Monografia

2. Record Nr. UNINA9910810977803321

Autore	Sangster Raymond C.
Titolo	Formation of silicon nitride from the 19th to the 21st century : a comprehensive summary and guide to the world literature / / Raymond C. Sangster ; updated and revised by David J. Fisher
Pubbl/distr/stampa	[Pfaffikon], Switzerland : , : Trans Tech Publications Ltd, , 2015 ©2015
ISBN	3-03826-901-8
Edizione	[Second edition, revised and updated.]
Descrizione fisica	1 online resource (1001 p.)
Collana	Materials Science Foundations ; ; Volumes 84-85
Disciplina	666
Soggetti	Silicon nitride
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references at the end of each chapters.
Nota di contenuto	Formation of Silicon Nitride from the 19th to the 21st Century; Preface; Table of Contents; Part A: In the Beginning; Part B: Technical Context of Silicon Nitride Formation; Part C: Si3N4 Products, Uses and Markets; Part D: Si3N4 by Reaction of Si(cr) Surfaces and N-Species; Part E: Si3N4 Powder Formation from Si(Powder)/N2(g); Part F: Fabrication of Reaction Bonded Silicon Nitride; Part G: Si3N4 from Si/N2 under Vigorous Conditions; Part H: Si3N4 Formation by Reaction of Si with N-Compounds; Part I: Si3N4 by Nitridation of Si-O Based Materials Part J: Si3N4 Formation from Si-N Based MaterialsPart K: Comparative Overview and Summary of Si3N4 CVD; Part L: Si3N4 by CVD Nitridation of Si-H Compounds; Part M: Si3N4 by CVD Nitridation of Si Halides and Halosilanes; Part N: Si3N4 Formation in Si-C-N Systems; Part O: Si3N4 Formation in Si-N-X Systems, X = B, P, S, Fe, other
Sommario/riassunto	The elements: Si, N, O, C and H, have strong chemical affinities for one another. Under the correct conditions, Si-N bonding will occur in almost any Si-N-(O/C/H), and many related, reaction systems; although Si-O and Si-C are formidable competitors to Si-N. The most favored Si-N compound is stoichiometric Si3N4. It comes in three common varieties. How they interrelate, how one finds them and (above all) how one makes them - and how sometimes they just happen to form - are the subjects of this book, with due attention being paid to closely related matters. This revised second edition summariz

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Record Nr.	UNIORUON00059655
Autore	WEGGEL, Oskar
Titolo	China-Volksrepublik / Oskar Weggel
Pubbl/distr/stampa	Hamburg, : [Institut fur Asienkunde], 197-
Descrizione fisica	p. 79-116 [37] p. ; 22 c
Classificazione	CIN IV B
Soggetti	CINA - STORIA - 1949-1976
Lingua di pubblicazione	Tedesco
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Estratto da : Handbuch der Dritten Welt 4 / hrsg. von Dieter Nohlen und Franz Nuschler.